## 國立中山大學 101 學年度碩士暨碩士專班招生考試試題

科目:電子學【海下海物所碩士班選

題號:4163

考】

共2頁第1頁

- 1. (18%) For the circuit in Fig. 1, find the values of  $i_I$ ,  $v_I$ ,  $i_I$ ,  $i_2$ ,  $v_o$ ,  $i_L$ , and  $i_o$ . Also find the voltage gain  $v_o/v_I$ , and the current gain  $i_L/i_I$ .
- 2. (20%) The 6.8-V zener diode in the circuit of Fig. 2 is specified to have  $V_Z = 6.8$  V at  $I_Z = 5$  mA,  $r_z = 20$   $\Omega$ , and  $I_{ZK} = 0.2$  mA. The supply voltage  $V^+$  is nominally 10 V but can vary by  $\pm 1$  V. (a) Find  $V_O$  with no load and with  $V^+$  at its nominal value. (b) Find the change in  $V_O$  resulting from the  $\pm 1$ -V change in  $V^+$ . (c) Find the change in  $V_O$  resulting from connecting a load resistance  $R_L$  that draws a current  $I_L = 1$  mA. (d) Find the change in  $V_O$  when  $R_L = 2$  k $\Omega$ . (e) Find the value of  $V_O$  when  $R_L = 0.5$  k $\Omega$ .
- 3. (16%) Figure 3 shows a discrete common-source MOSFET amplifier utilizing the drain-to-gate feedback biasing arrangement. Determine the small-signal voltage gain  $v_o/v_i$ , and the input resistance  $R_{\rm in}$ . The transistor has  $V_t = 1.5 \text{ V}$ ,  $k'_n(W/L) = 0.25 \text{ mA/V}^2$ , and  $V_A = 50 \text{ V}$ . Assume the coupling capacitors to be sufficiently large so as to act as short circuits at the signal frequencies of interest.
- 4. (15%) A piezoelectric crystal, such as quartz, exhibits electromechanical-resonance characteristics that are very stable and high Q factors. The circuit symbol of a crystal is shown in Fig. 4(a) and its equivalent circuit model is given in Fig. 4(b). A 2-MHz quartz crystal is specified to have L = 0.52 H,  $C_s = 0.012$  pF,  $C_p = 4$  pF, and r = 120  $\Omega$ . Find the series resonance frequency  $f_s$ , parallel resonance frequency  $f_p$ , and the Q factor.
- 5. (15%) For the class B output stage of Fig. 5, let  $V_{CC} = 6$  V and  $R_L = 4 \Omega$ . If the output is a sinusoid with 4.5-V peak amplitude, find (a) the output power; (b) the average power drawn from each supply; (c) the power efficiency obtained at this output voltage; (d) the peak currents supplied by  $v_I$ , assuming that  $\beta_N = \beta_P = 50$ ; (e) the maximum power that each transistor must be capable of dissipating safely.
- 6. (16%) For a pn junction with  $N_A = 10^{17}/\text{cm}^3$  and  $N_D = 10^{16}/\text{cm}^3$ , find, at T = 300 K, the built-in voltage, the width of the depletion region, and the distance it extends in the p side and in the n side of the junction. Use  $n_i = 1.5 \times 10^{10}/\text{cm}^3$ .

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共2頁第2頁

考】

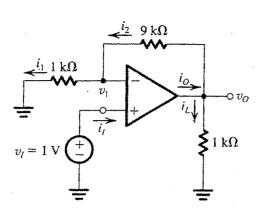


Fig. 1

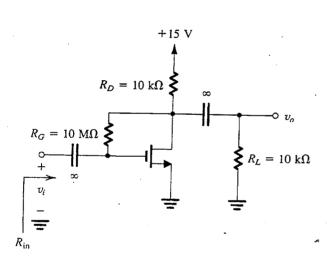


Fig. 3

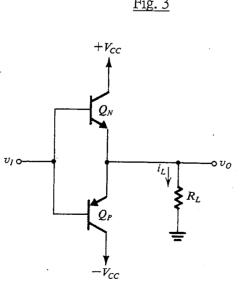


Fig. 5

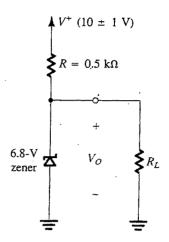


Fig. 2

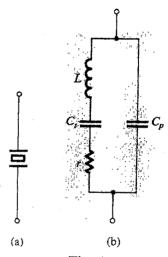


Fig. 4